

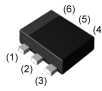
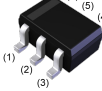
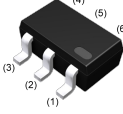
<For Tr1(NPN)>

Parameter	Value
V_{CEO}	50V
I_C	150mA

<For Tr2(PNP)>

Parameter	Value
V_{CEO}	-50V
I_C	-150mA

● Outline

<p>SOT-563</p>  <p>EMZ1 (EMT6)</p>	<p>SOT-363</p>  <p>UMZ1N (UMT6)</p>
<p>SOT-457</p>  <p>IMZ1A (SMT6)</p>	

● Features

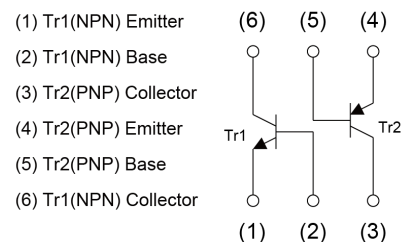
- 1) Both a 2SA1037AK chip and a 2SC2412K chip in a EMT or UMT or SMT package.
- 2) Mounting possible with EMT3 or UMT3 or SMT3 automatic mounting machines.
- 3) Transistor elements are independent, eliminating interference.
- 4) Mounting cost and area can be cut in half.

● Application

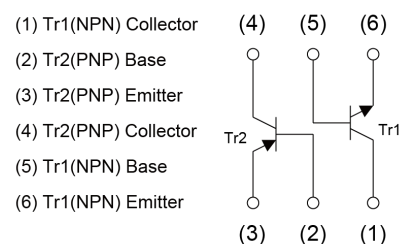
GENERAL PURPOSE SMALL SIGNAL AMPLIFIER

● Inner circuit

EMZ1 / UMZ1N



IMZ1A



● Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
EMZ1	SOT-563 (EMT6)	1616	T2R	180	8	8000	Z1
UMZ1N	SOT-363 (UMT6)	2021	TR	180	8	3000	Z1
IMZ1A	SOT-457 (SMT6)	2928	T108	180	8	3000	Z1

●絶対最大定格 ($T_a = 25^\circ\text{C}$)

項目	記号	Tr1(NPN)	Tr2(PNP)	単位
コレクタ・ベース間電圧	V_{CBO}	60	-60	V
コレクタ・エミッタ間電圧	V_{CEO}	50	-50	V
エミッタ・ベース間電圧	V_{EBO}	7	-6	V
コレクタ電流	I_C	150	-150	mA
許容損失	EMZ1/ UMZ1N	P_D^{*1*2}	150	mW/Total
	IMZ1A	P_D^{*1*3}	300	mW/Total
ジャンクション温度	T_j	150		$^\circ\text{C}$
保存温度	T_{stg}	-55 ~ +150		$^\circ\text{C}$

●電気的特性 ($T_a = 25^\circ\text{C}$) <Tr1(NPN)>

項目	記号	条件	最小値	標準値	最大値	単位
コレクタ・ベース降伏電圧	BV_{CBO}	$I_C = 50\mu\text{A}$	60	-	-	V
コレクタ・エミッタ降伏電圧	BV_{CEO}	$I_C = 1\text{mA}$	50	-	-	V
エミッタ・ベース降伏電圧	BV_{EBO}	$I_E = 50\mu\text{A}$	7	-	-	V
コレクタ遮断電流	I_{CBO}	$V_{CB} = 60\text{V}$	-	-	100	nA
エミッタ遮断電流	I_{EBO}	$V_{EB} = 7\text{V}$	-	-	100	nA
コレクタ・エミッタ飽和電圧	$V_{CE(sat)}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$	-	-	400	mV
直流電流増幅率	h_{FE}	$V_{CE} = 6\text{V}, I_C = 1\text{mA}$	120	-	560	-
利得帯域幅積	f_T	$V_{CE} = 12\text{V}, I_E = -2\text{mA}, f = 100\text{MHz}$	-	180	-	MHz
コレクタ出力容量	C_{ob}	$V_{CB} = 12\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$	-	2.0	3.5	pF

●電気的特性 ($T_a = 25^\circ\text{C}$) <Tr2(PNP)>

項目	記号	条件	最小値	標準値	最大値	単位
コレクタ・ベース降伏電圧	BV_{CBO}	$I_C = -50\mu\text{A}$	-60	-	-	V
コレクタ・エミッタ降伏電圧	BV_{CEO}	$I_C = -1\text{mA}$	-50	-	-	V
エミッタ・ベース降伏電圧	BV_{EBO}	$I_E = -50\mu\text{A}$	-6	-	-	V
コレクタ遮断電流	I_{CBO}	$V_{CB} = -60\text{V}$	-	-	-100	nA
エミッタ遮断電流	I_{EBO}	$V_{EB} = -6\text{V}$	-	-	-100	nA
コレクタ・エミッタ飽和電圧	$V_{CE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$	-	-	-500	mV
直流電流増幅率	h_{FE}	$V_{CE} = -6\text{V}, I_C = -1\text{mA}$	120	-	560	-
利得帯域幅積	f_T	$V_{CE} = -12\text{V}, I_E = 2\text{mA}, f = 100\text{MHz}$	-	140	-	MHz
コレクタ出力容量	C_{ob}	$V_{CB} = -12\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$	-	4.0	5.0	pF

*1 各端子を参考ランドに実装した場合

*2 一素子当たり120mWを超えないこと

*3 一素子当たり200mWを超えないこと

●電氣的特性曲線 (Ta=25°C) <Tr1(NPN)>

Fig.1 Ground Emitter Propagation Characteristics

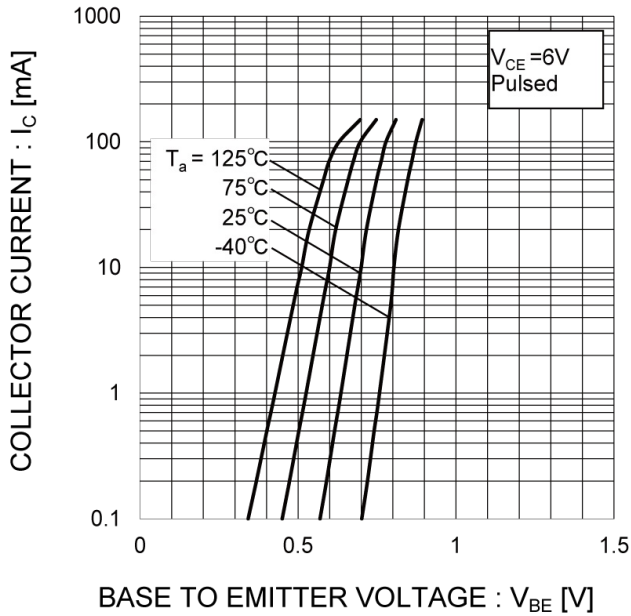


Fig.2 Grounded Emitter Output Characteristics

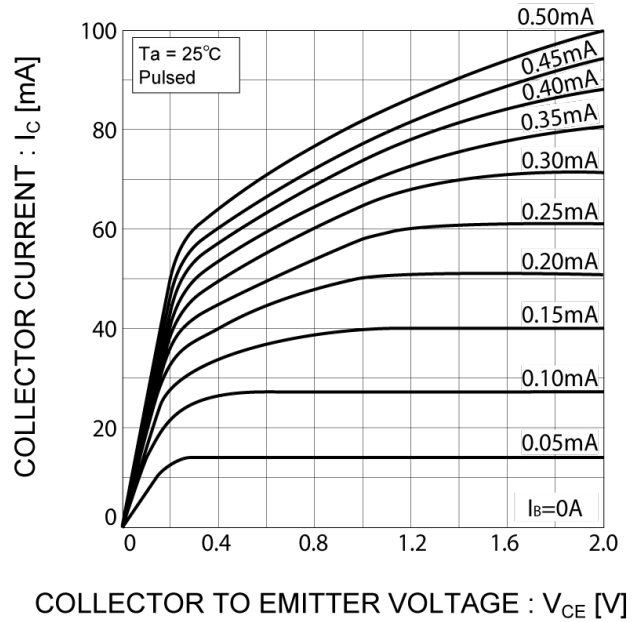


Fig.3 DC Current Gain vs. Collector Current (I)

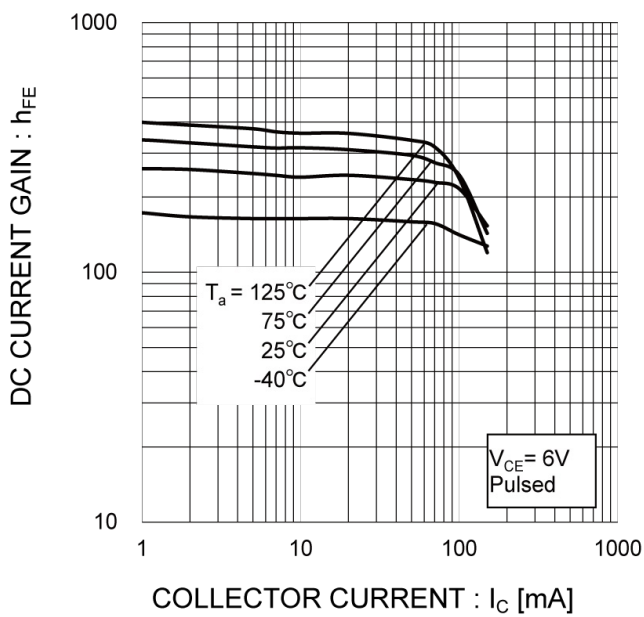
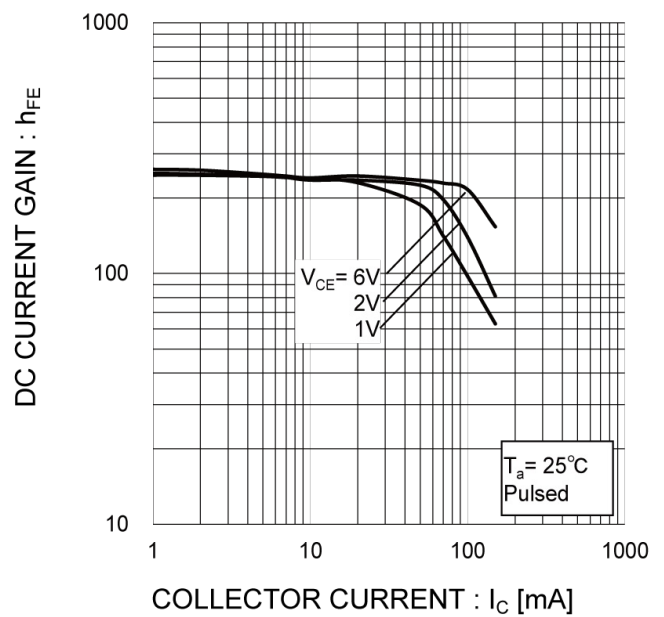


Fig.4 DC Current Gain vs. Collector Current (II)



● Electrical characteristic curves ($T_a=25^\circ\text{C}$) <For Tr1(NPN)>

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I_c)

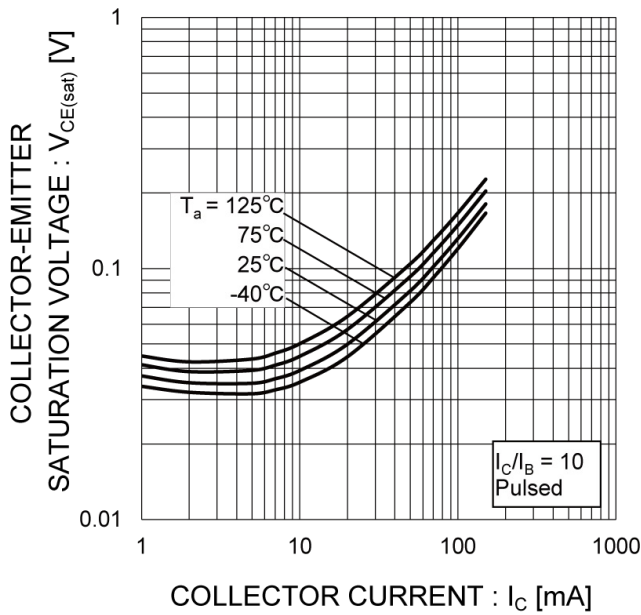


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (I_c)

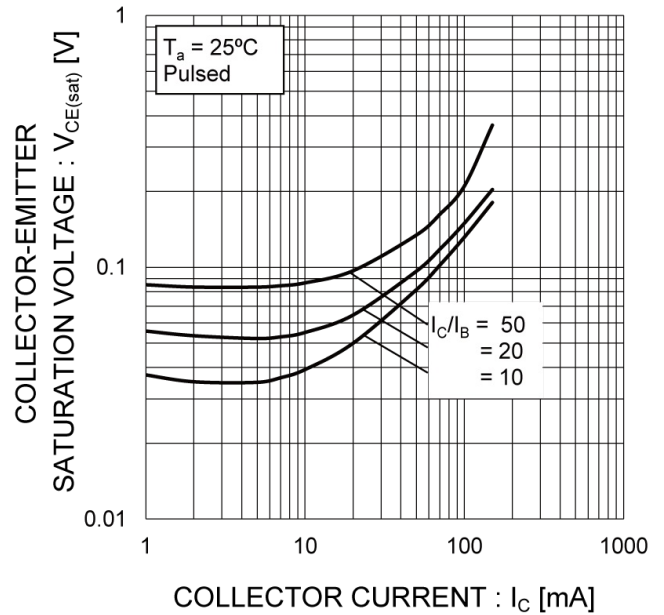


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current (I_c)

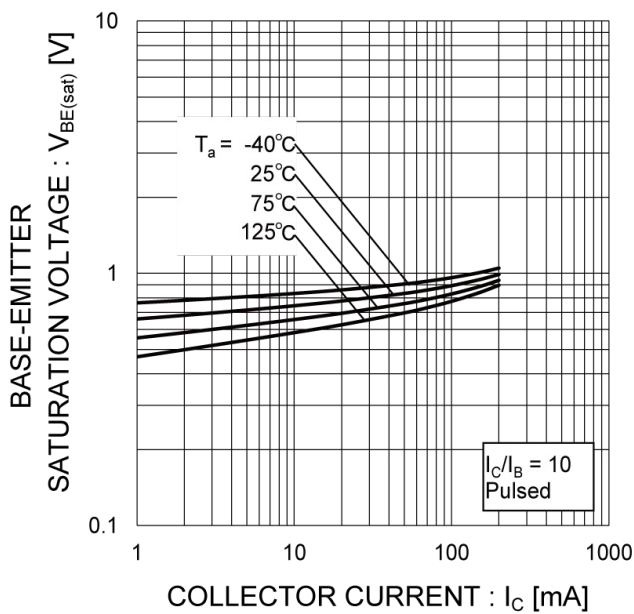
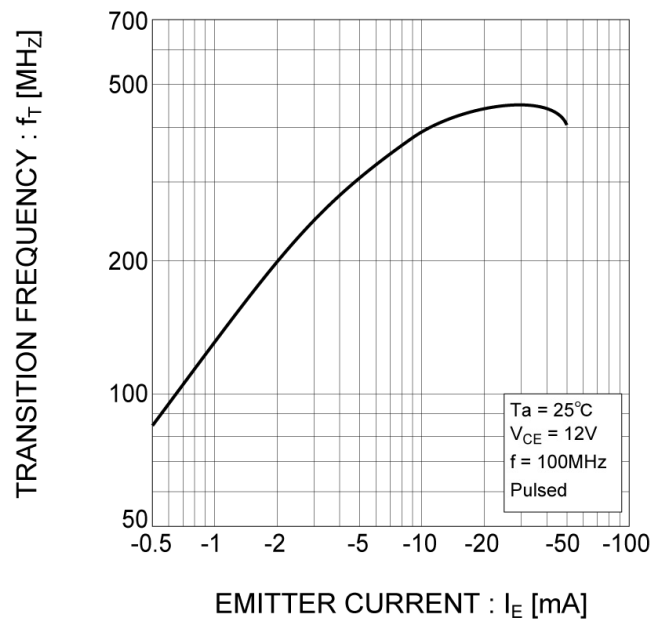


Fig.8 Gain Bandwidth Product vs. Emitter Current



●Electrical characteristic curves($T_a=25^\circ\text{C}$) <For Tr1(NPN)>

Fig.9 Collector Output Capacitance vs. Collector-Base Voltage
Emitter Input Capacitance vs. Emitter-Base Voltage

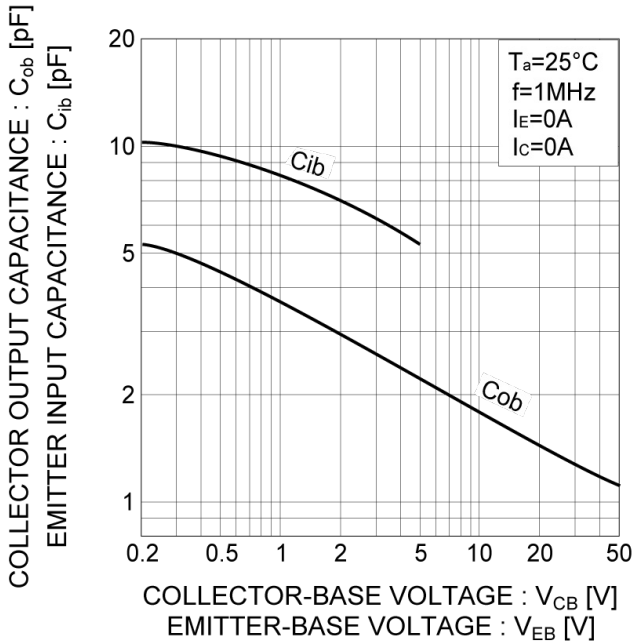


Fig.10 Safe Operating Area

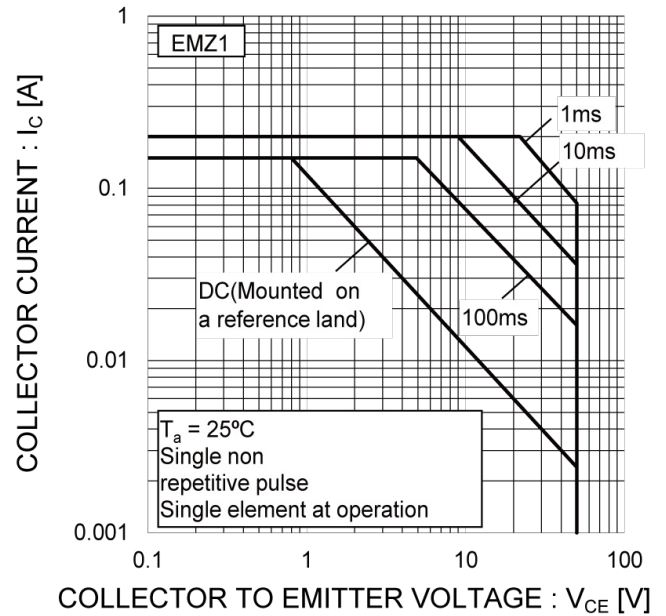


Fig.11 Safe Operating Area

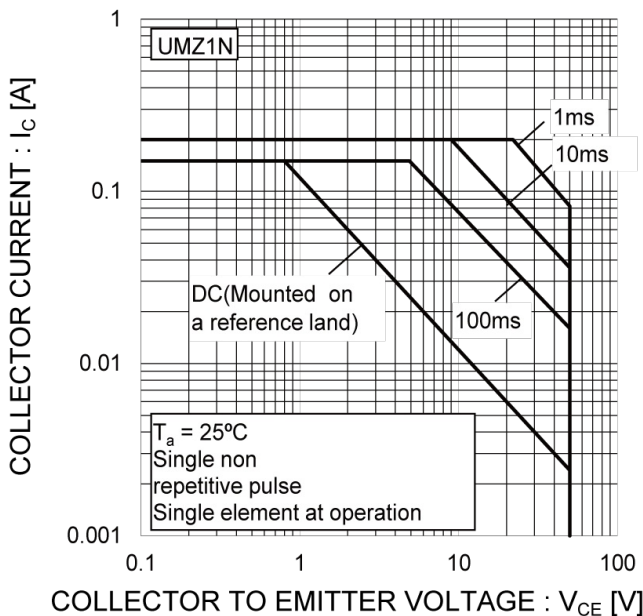
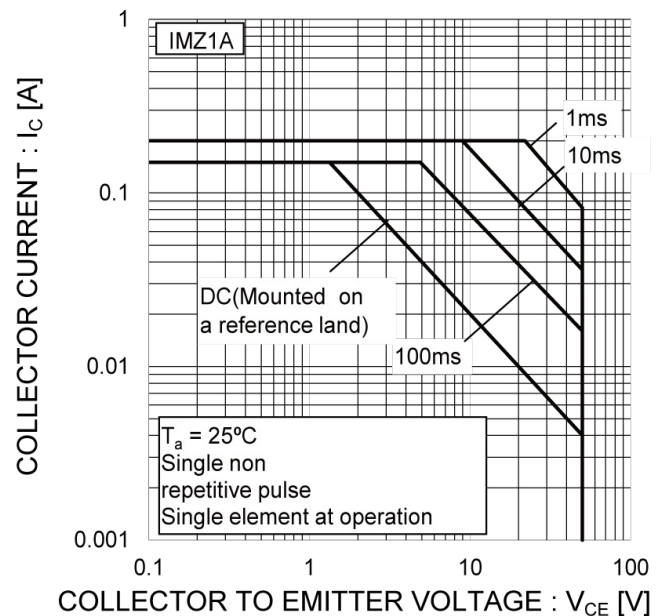


Fig.12 Safe Operating Area



●Electrical characteristic curves($T_a=25^{\circ}\text{C}$ <For Tr2(PNP)>

Fig.13 Ground Emitter Propagation Characteristics

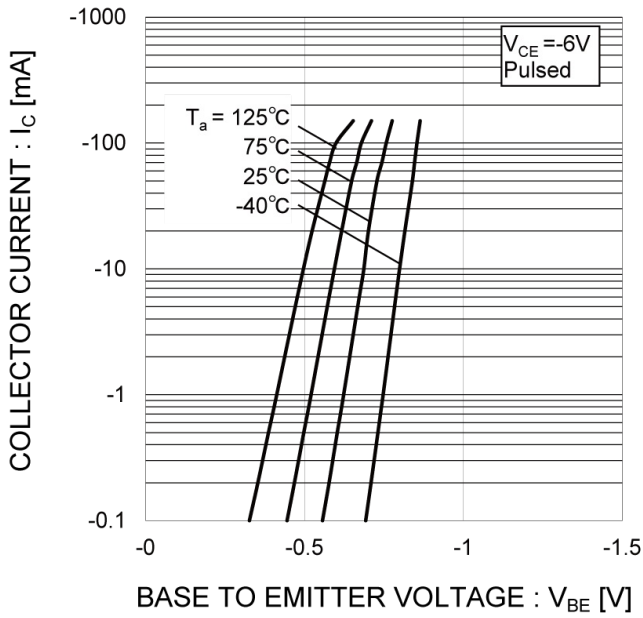


Fig.14 Grounded Emitter Output Characteristics

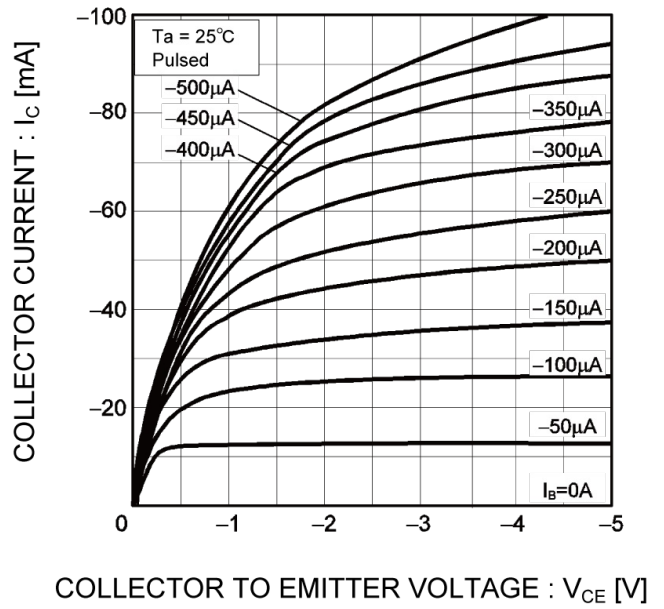


Fig.15 DC Current Gain vs. Collector Current (I)

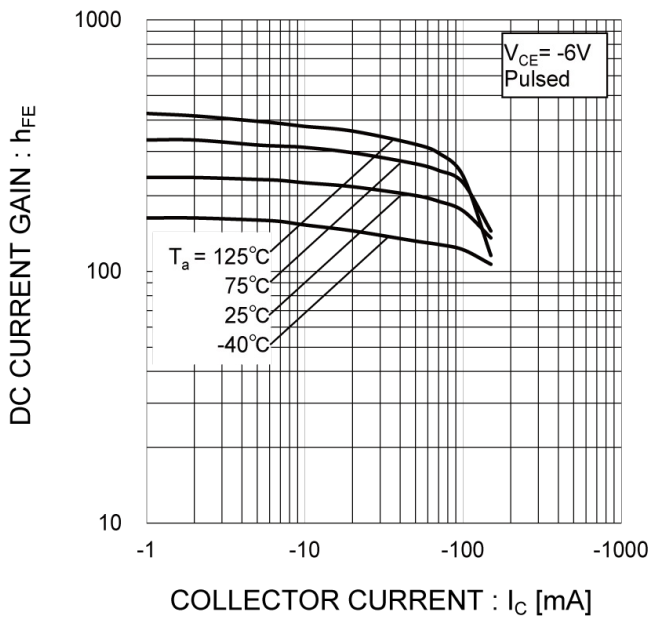
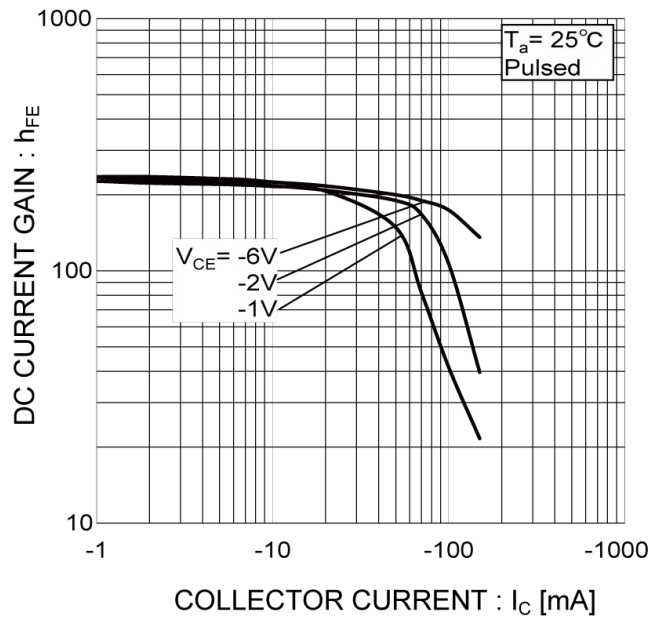


Fig.16 DC Current Gain vs. Collector Current (II)



● Electrical characteristic curves ($T_a = 25^\circ\text{C}$) <For Tr2(PNP)>

Fig.17 Collector-Emitter Saturation Voltage vs. Collector Current(I)

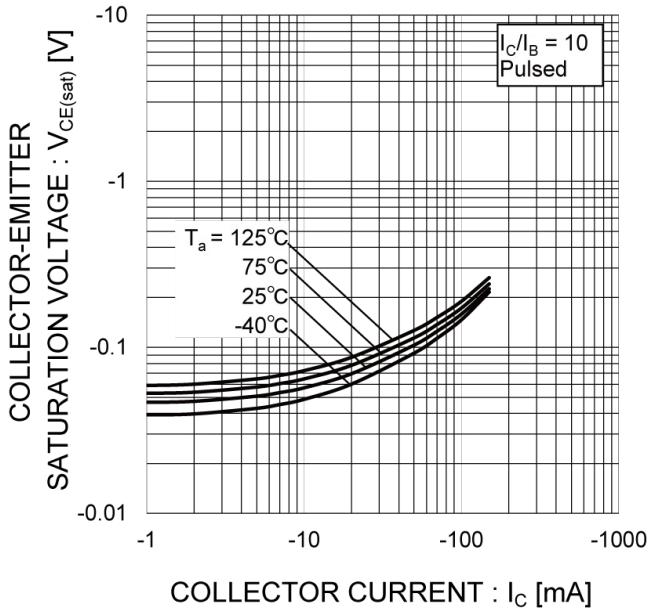


Fig.18 Collector-Emitter Saturation Voltage vs. Collector Current (I)

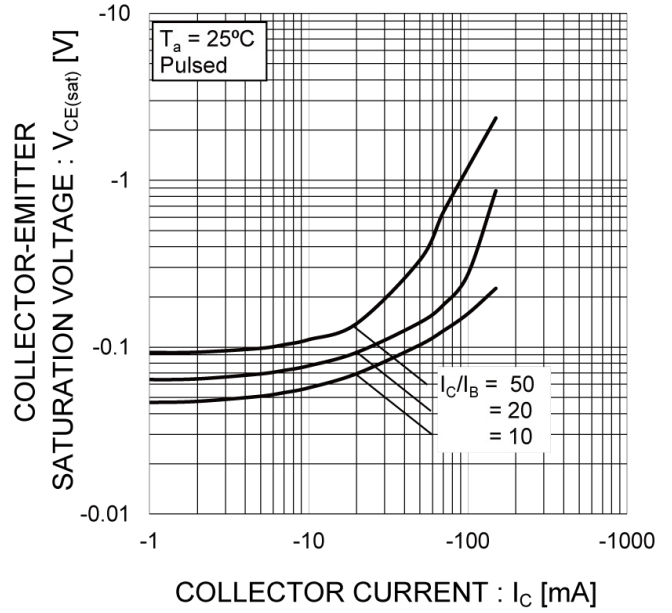


Fig.19 Base-Emitter Saturation Voltage vs. Collector Current (I)

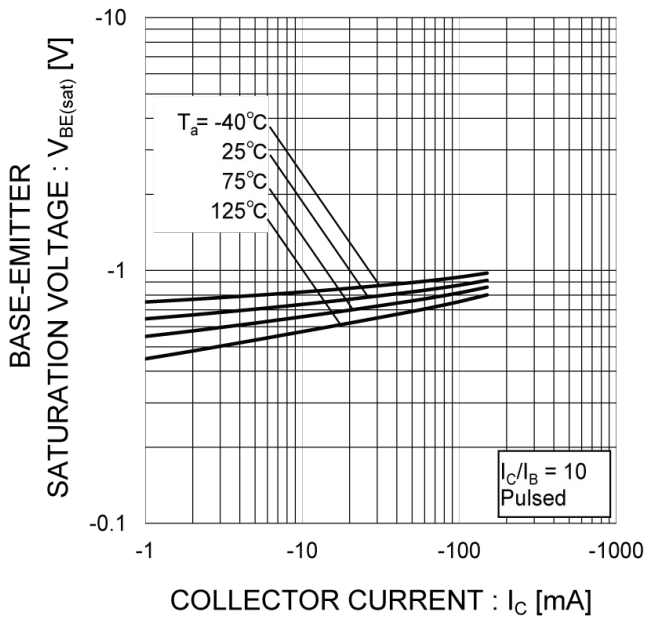
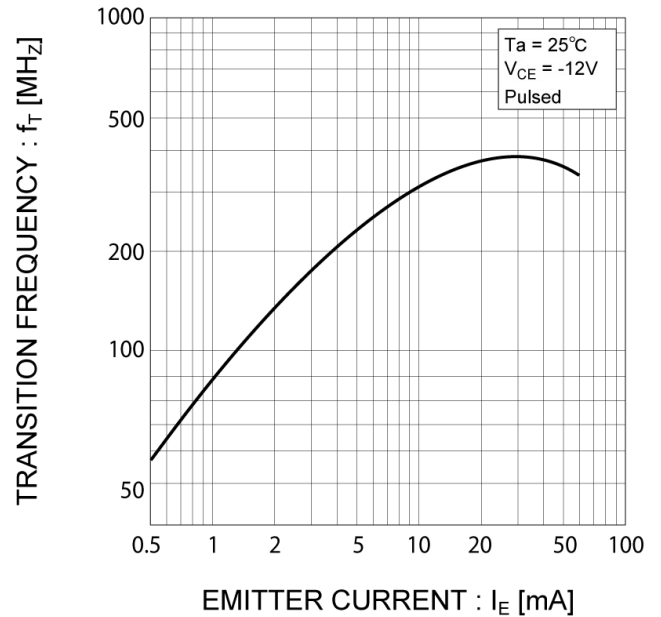


Fig.20 Gain Bandwidth Product vs. Emitter Current



●Electrical characteristic curves($T_a = 25^\circ\text{C}$) <For TR2(PNP)>

Fig.21 Collector Output Capacitance vs. Collector-Base Voltage
Emitter Input Capacitance vs. Emitter-Base Voltage

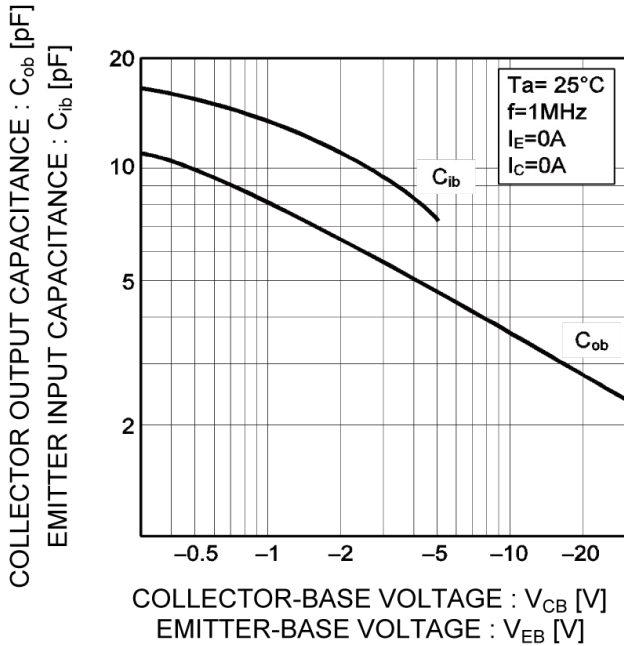


Fig.22 Safe Operating Area

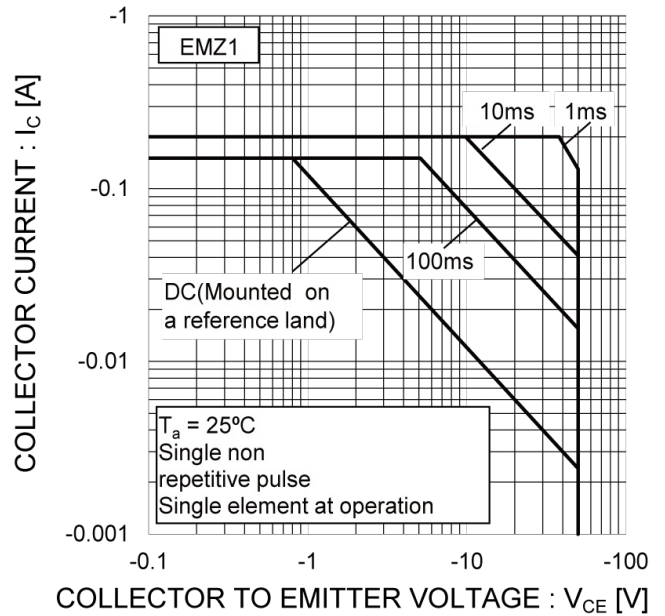


Fig.23 Safe Operating Area

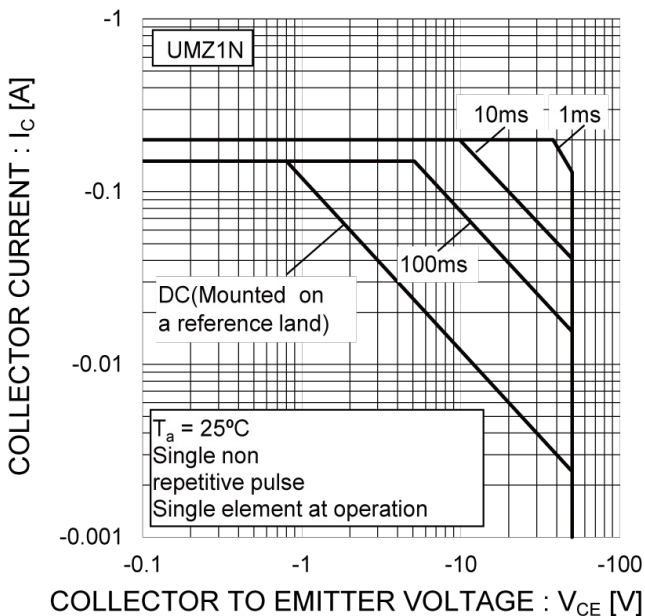
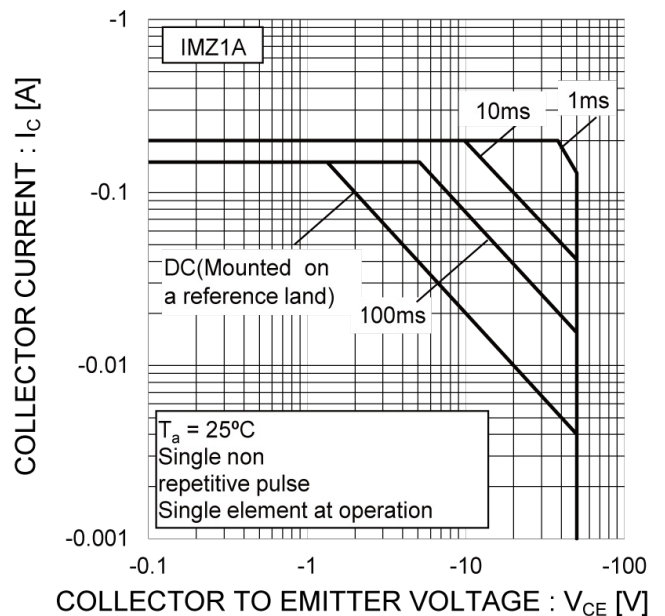
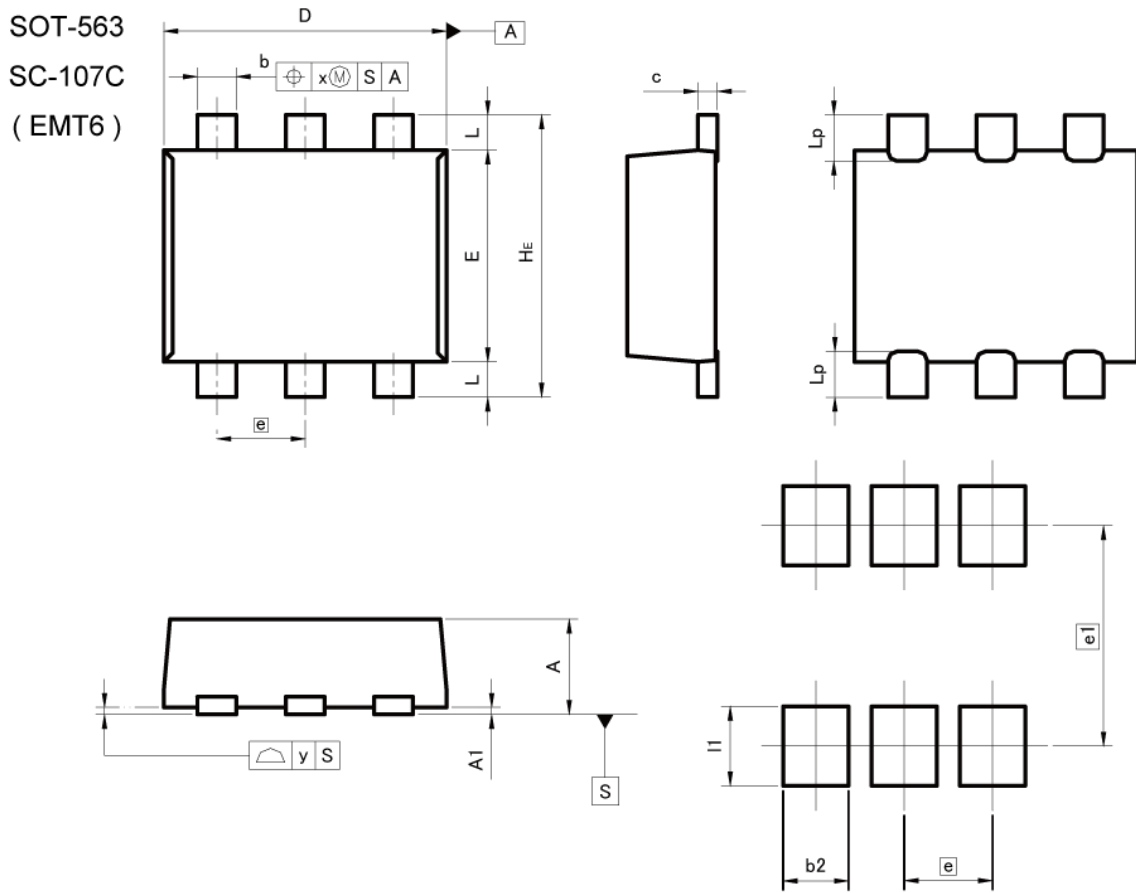


Fig.24 Safe Operating Area



●Dimensions



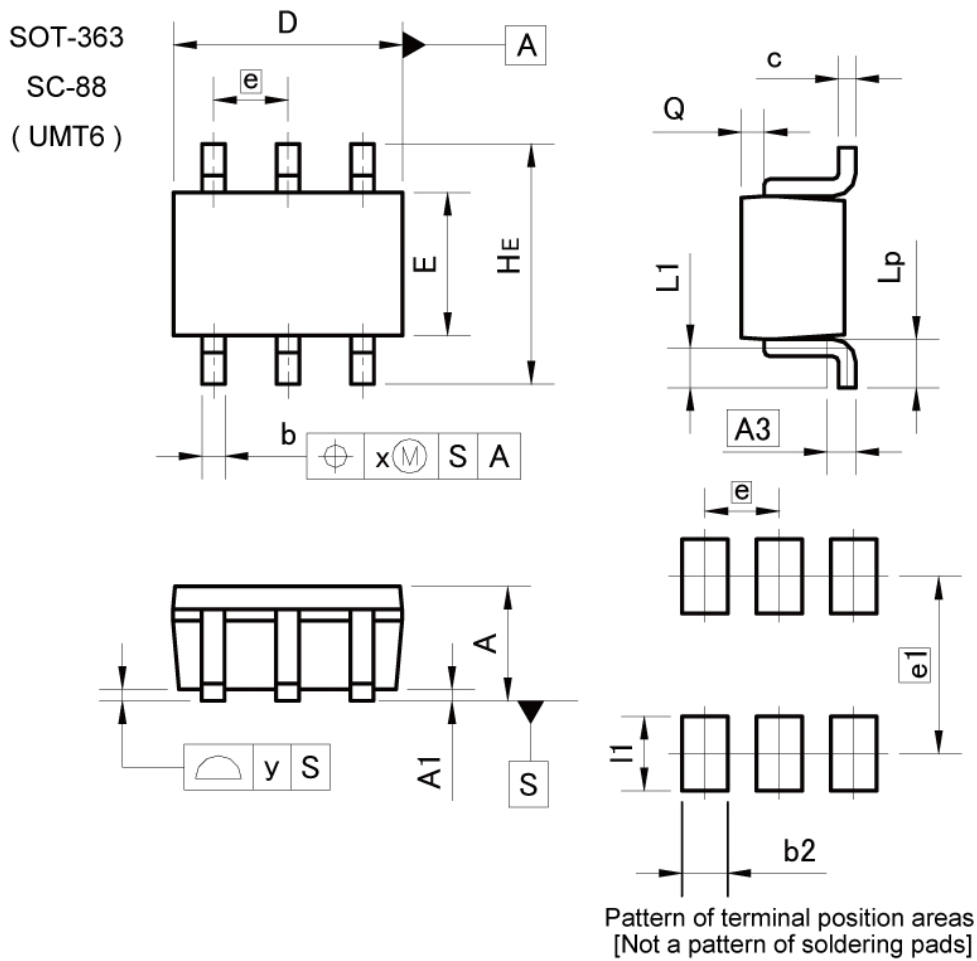
Pattern of terminal position areas
[Not a pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.45	0.55	0.018	0.022
A1	0.00	0.10	0.000	0.004
b	0.17	0.27	0.007	0.011
c	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	1.10	1.30	0.043	0.051
e	0.50		0.020	
HE	1.50	1.70	0.059	0.067
L	0.10	0.30	0.004	0.012
Lp	-	0.35	-	0.014
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.37	-	0.015
e1	1.25		0.049	
I1	-	0.45	-	0.018

Dimension in mm/inches

●Dimensions



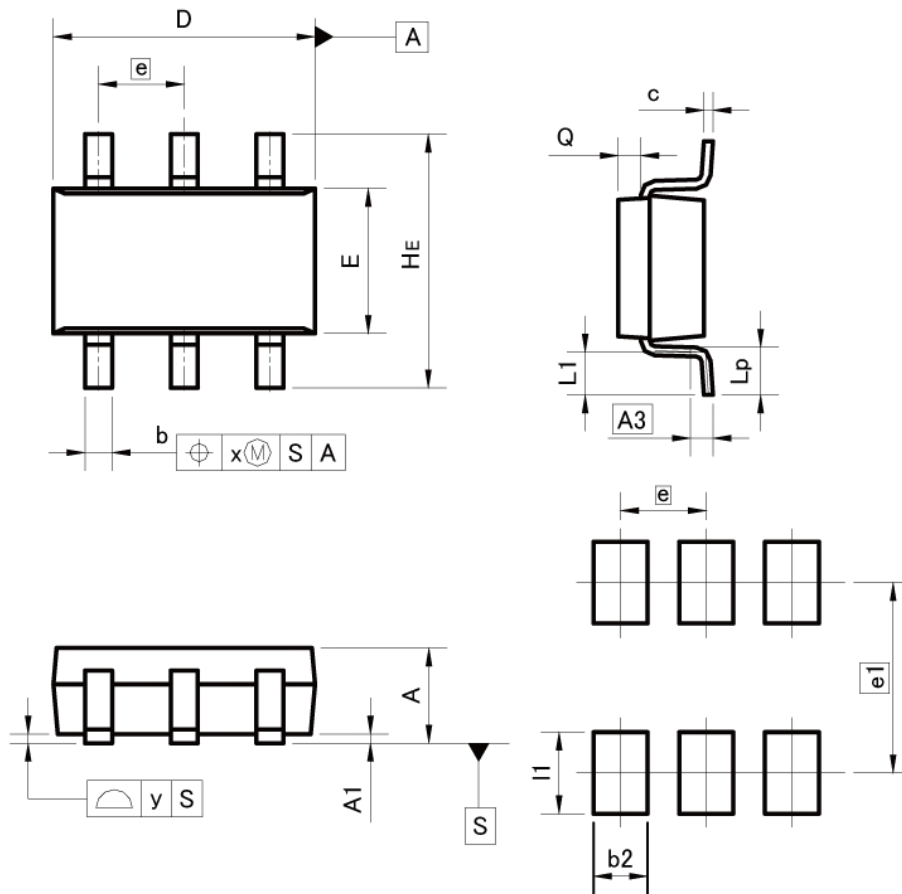
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.80	1.00	0.031	0.039
A1	0.00	0.10	0.000	0.004
A3	0.25		0.010	
b	0.15	0.30	0.006	0.012
c	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
e	0.65		0.026	
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.40	-	0.016
e1	1.55		0.061	
I1	-	0.65	-	0.026

Dimension in mm/inches

●Dimensions

SOT-457
SC-74
(SMT6)



Pattern of terminal position areas
[Not a pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
A3	0.25		0.010	
b	0.25	0.40	0.010	0.016
c	0.09	0.25	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
x	-	0.20	-	0.008
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.60	-	0.024
e1	2.10		0.083	
I1	-	0.90	-	0.035

Dimension in mm/inches

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